

BST08B64GA1

1. Product Overview

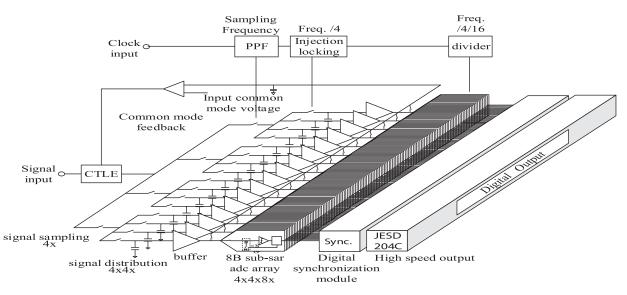
BST08B64GA1 is an 8-bit ultra-high-speed A/D converter with an adjustable sampling rate range of 32GSPS to 64GSPS and an input bandwidth of about 19GHz. The ADC core is implemented using a time-interleaved SAR structure. By using broadband sample-and-hold circuit design technology, time interleaving and internal error correction technology, and JESD204C high-speed serial interface circuit design technology, it has the ability of a single-chip high-speed and high-input bandwidth A/D converter, while having a low bit error rate (CER<1e-14).

The BST08B64GA1 is available in a BGA484 package and is rated over the −40°C to +85°C industrial temperature range. The recommended ambient operating temperature is Below 50 degrees, thus ensuring the junction temperature inside the chip is less than 100 degrees, thereby obtaining better performance and stability.

2. Product Features

- NSD: -141.6 dBFS/Hz at 50 GSPS with -1dBFS, 1GHz input;
 -142.0 dBFS/Hz at 50 GSPS with -3dBFS, 1GHz input.
- SFDR: 51.3 dBFS at 50 GSPS with -1dBFS, 1GHz input;
 47.5 dBFS at 50 GSPS with -1dBFS, 10GHz input;
 - 42.2 dBFS at 50 GSPS with -1dBFS, 20GHz input.
- Worst other spur (H2, H3 Except for: 5 1.3 dBFS at 50 GSPS with -1dBFS, 1GHz input.
- DNL Typical value ±0.16 LSB; INL Typical value ±0.46 LSB.
- Low bit error rate (C E R) : $< 1 \times 10^{-14}$ (see Table 1 0 for test conditions).
- Low power consumption: typical value <= 4W at 50 GSPS.
- Input bandwidth supports 19GHz About 500mVpp, 100Ω.
- Support SPI Interface, meet SPI Standard interface protocol, addressable internal storage space.
- 32 Lane JESD204C Output, maximum line rate up to 25Gbps, compatible with JESD204B interface.
- 19 × 19mm, 484-ball BGA package.

3. Functional Block Diagram





4. Electrical Parameters

4.1. Technical specifications

Unless otherwise specified, DVDD = DRVDD1 = 1.0V, AVDD = 1.1V, DRVDD2 = SVDDH = 2.5V, AIN = -1.0dBFS.

Table 1. Specifications

	Tamanawatuwa		BST08B64GA1		Unit
Parameter	Temperature	Minimum	Typical	Maximum	
Speed Grade		32	50	64	GSPS
Resolution		8			Bit
	Accuracy	,			
No missing codes	Room temperature		ensure		
Offset error range	Room temperature		-3 ~ 3		LSB
Gain error range	Room temperature		-10 ~ 10		%FSR
Differential Nonlinearity (DNL)	Room temperature		±0.16		LSB
Integral Nonlinearity (INL)	Room temperature		±0.46		LSB
	Analog Inp	ut			
Differential input voltage	Room temperature		450~580		mVpp
Differential input resistance	Room temperature		81		Ω
Input common mode voltage (Vcm)	Room temperature	0.5 ~ 0.9			V
Full power analog bandwidth	Room temperature	19			GHz
Input Referred Noise	Room temperature	0.8			LSB _{RMS}
	Isolation				
Between analog power supply and digital power supply	Room temperature	ature FEXT, NEXT <- 50 dB(0~10GHz)			_
	power supp	oly			
D_{VDD}	Room temperature	0.975	1.0	1.025	V
A_{VDD}	Room temperature	1.080	1.1	1.120	V
D _{RVDD} 1	Room temperature	0.975	1.0	1.025	V
D_{RVDD}^2	Room temperature	2.45	2.5	2.75	V
S _{VDDH}	Room temperature	1.8	2.5	2.75	V
l _{DVDD} 1	Room temperature	0.6	Α		
I _{AVDD} 1	Room temperature	8.0	Α		
I _{DRVDD1} 1	Room temperature	0.9	А		
I _{DRVDD2} 1	Room temperature	0.6	А		
I _{svddh} 1	Room temperature	0.01	А		
Power consumption1	Room temperature	4.0	W		

 $Note \ 1: Note \ 1 in the \ table \ Is \ the \ current \ and \ power \ consumption \ at \ 50G \ Sampling \ rate, \ 16-lane \ The \ following \ test \ results.$



4.1.1. Digital specifications

Unless otherwise specified, DVDD = DRVDD1 = 1.0V, AVDD = 1.1V, DRVDD2 = SVDDH = 2.5V, AIN = -1.0dBFS.

Table 2. Digital specifications

Parameter	Test conditions	Temperature	Typical Value	Unit			
	Clock	Input					
Differential input voltage		Room temperature	1400	mVpp			
Common mode input voltage		Room temperature	0.5	V			
Input resistance (differential)		Room temperature	105	Ω			
SYSREF enter (SYSREF_x)							
Differential input voltage		Room temperature	1000	mVpp			
Common mode input voltage		Room temperature	0.85	V			
Input resistance (differential)		Room temperature	103	Ω			
Input Capacitance		Room temperature	0.5	pF			
TRIG Input (TRIG_x)		Room temperature	1000	mVpp			
	Differential in	nput voltage	-				
Common mode input voltage		Room temperature	0.85	V			
Input resistance (differential)		Room temperature	105	Ω			
Input Capacitance		Room temperature	0.5	pF			
	Logic input (MO	SI, SCLK, CEB)					
Logic Compatibility		Room temperature	CMOS				
Voltage Logic 1		Room temperature	>0.7*SVDDH	V			
Voltage logic 0		Room temperature	<0.3*SVDDH	V			
Input resistance		Room temperature	44	kΩ			
Input Capacitance		Room temperature	1.5	pF			
	SYNCINE	B_x enter	'				
Logic Compatibility		Room temperature	CML				
Voltage		Room temperature	1000	mV			
Input resistance (differential)		Room temperature	32	kΩ			
Input Capacitance		Room temperature	1	pF			
	Logic outp	out (MISO)	-				
Logic Compatibility		Room temperature	CMOS				
Voltage Logic 1		Room temperature	>SVDDH - 0.45	V			
Voltage logic 0		Room temperature	<0.45	V			
	Reset (RSTB)					
Voltage Logic 1		Room temperature	>0.7*SVDDH	V			
Voltage logic 0		Room temperature	<0.3*SVDDH	V			
Input resistance (differential)		Room temperature	44	kΩ			
Input Capacitance		Room temperature	1.5	pF			
REFCLK Input (REFCLK_x)							
Differential input voltage		Room temperature	1000	mVpp			
Common mode input voltage		Room temperature	0.85	V			
Input resistance (differential)		Room temperature	100	Ω			
Input Capacitance		Room temperature	0.5	pF			
EXT_CLK enter							
Input voltage		Room temperature	2.5	V			
Input resistance		Room temperature	10	kΩ			
iliput resistance			10	1122			



4.1.2. Switch Specifications

Unless otherwise specified, DVDD = DRVDD1 = 1.0V, AVDD = 1.1V, DRVDD2 = SVDDH = 2.5V, AIN = -1.0dBFS.

Table 3. Switch Specifications

Parameter	Test conditions	Temperature	Minimum	Typical	Maximum	Unit		
	Clock (CLK)							
Clock rate		Room temperature	8		16	GSPS		
Clock Duty Cycle		Room temperature	45	50	55	% Duty Cycle		
Uncertain (jitter)		Room temperature	50			(fs) rms		
	Latency							
Pipeline Delay		Room temperature	4672			Clock cycle		
TRIG(TRIG_x)								
Build Time		Room temperature	mperature 1			ns		
Keep Time		Room temperature	1			ns		
Uncertain (jitter)		Room temperature	2			(ps) rms		
Output Parameters (Serdout)								
Rise time		Room temperature	10			ps		
Fall time		Room temperature	10			ps		
Line Rate		Room temperature			25	Gbps		

4.1.3. Timing Specifications

Table 4. Timing Specifications

Parameter	Test Conditions / Comments	Minimum	Typical Value	Maximum	Unit		
	SPI Timing requirements						
TdS	Data and SCLK Setup time between rising edges	8			ns		
Td	Data and SCLK Hold time between rising edges	8			ns		
Tclk	SCLK cycle	100			ns		
Ts	CEB With SCLK The build time between	4			ns		
Th	CEB With SCLK Keep time between	4			ns		
Thigh	SCLK The minimum time that the	20			ns		
Tlow	SCLK The minimum time that it should be in the logic low state	20			ns		
Taccess	SCLK Between the falling edge and the read instruction outputting valid data Maximum delay time		12	20	ns		



5. Ordering Information

Serial number	Model	Package	Packaging materials	Device level
1	BST08B64GA1PBGA484I	PBGA484	Plastic packaging	I class
2	BST08B64GA1PBGA484M3	PBGA484	Plastic packaging	N1 class
3	BST08B64GA1PBGA484E	PBGA484	Plastic packaging	Military Temperature

Note 1:

- a) I/ Industrial temperature range devices meet the screening requirements of Q/BST40022-2021 "General Specifications for Industrial Temperature Range Products of Huawei", and their operating environment temperature range should be -40 $^{\circ}$ C $^{\sim}$ +85 $^{\circ}$ C.
- b) N/N1 grade devices meet GJB 7400 Screening requirements for level N/N1 of the General Specification for Semiconductor Integrated Circuits for Qualified Manufacturer Certification.
- c) Military temperature grade devices meet Q/BST40020-2018 According to the screening requirements of "General Specifications for HUAWEI Military-grade Products", the operating environment temperature range should be -55 $^{\circ}$ C $^{\circ}$ +125 $^{\circ}$ C.

Note 2: The product ordering information is for our existing products or devices that have been confirmed to be developed. We can develop devices in other packaging forms according to user needs.